Listing of Claims:

42. (Currently Amended) An in-plane switching liquid crystal display device comprising:

first and second substrates;

a plurality of gate and data bus lines on the first substrate, the gate lines being crossed with the data bus lines;

a common line parallel to any one of the gate lines and the data bus lines on the first substrate;

a gate insulator on the first substrate; and

a transparent first metal layer and a transparent second metal layer <u>directly</u> on the gate insulator[[.]];

a plurality of thin film transistors at crossing points of the gate and data bus lines;

a passivation layer formed substantially on the common line and thin film transistors.

43. (Cancelled)

and

44. (Currently Amended) The device of claim [[43]]42, wherein each of the thin film transistors include:

a gate electrode on the first substrate;

a semiconductor layer on the gate electrode; and

source and drain electrodes on the semiconductor layer.

- 45. (Previously Presented) The device of claim 44, wherein the transparent first metal layer is connected to the drain electrodes.
- 46. (Original) The device of claim 42, wherein the transparent second metal layer is connected to the common line.



- 47. (Original) The device of claim 42, wherein the common line and the transparent first metal layer form a first storage capacitor.
- 48. (Original) The device of claim 42, wherein the transparent first metal layer and the transparent second metal layer form a second storage capacitor.
- 49. (Original) The device of claim 42, wherein the transparent first metal layer includes a data electrode and the transparent second metal layer includes a common electrode.



- 50. (Original) The device of claim 42, wherein the transparent first and second metal layers include indium tin oxide.
- 51. (Original) The device of claim 42, further comprising a first alignment layer on the first substrate.
- 52. (Original) The device of claim 51, wherein the first alignment layer includes one of polyimide, polyamide, polyvinylcinnamate, and polysiloxanecinnamate.
 - 53. (Original) The device of claim 42, further comprising:
 - a black matrix layer on the second substrate;
 - a color filter on the black matrix layer; and
 - a liquid crystal layer between the first and second substrates.
- 54. (Original) The device of claim 42, further comprising a second alignment layer on the second substrate.
- 55. (Original) The device of claim 54, wherein the second alignment layer includes one of polyimide, polyamide, polyvinylcinnamate, and polysiloxanecinnamate.

56. (Currently Amended) A method of forming an in-plane switching liquid crystal display device, comprising:

forming first and second substrates;

forming a plurality of gate and data bus lines on the first substrate, the gate lines being crossed with the data bus lines;

forming a common line in parallel to any one of the gate lines and the data bus lines on the first substrate;

forming a gate insulator on the first substrate; and

forming a transparent first metal layer and a transparent second metal layer directly on the gate insulator[[.]];

forming a plurality of thin film transistors at crossing points of the gate and data bus lines; and

forming a passivation layer substantially on the common line and thin film transistors.

57. (Cancelled)

58. (Currently Amended) The method of claim [[57]]56, wherein each of the thin film transistors include:

a gate electrode on the first substrate;

a semiconductor layer on the gate electrode; and

source and drain electrodes on the semiconductor layer.

- 59. (Previously Presented) The method of claim 58, wherein the transparent first metal layer is connected to the drain electrodes.
- 60. (Previously Presented) The method of claim 56, wherein the transparent second metal layer is connected to the common line.



- 61. (Previously Presented) The method of claim 56, wherein the common line and the transparent first metal layer form a first storage capacitor.
- 62. (Previously Presented) The method of claim 56, wherein the transparent first metal layer and the transparent second metal layer form a second storage capacitor.
- 63. (Previously Presented) The method of claim 56, wherein the transparent first metal layer includes a data electrode and the transparent second metal layer includes a common electrode.
- 64. (Previously Presented) The method of claim 56, wherein the transparent first and second metal layers include indium tin oxide.
- 65. (Previously Presented) The method of claim 56, further comprising forming a first alignment layer on the first substrate.
- 66. (Previously Presented) The method of claim 65, wherein the first alignment layer includes one of polyimide, polyamide, polyvinylcinnamate, and polysiloxanecinnamate.
 - 67. (Previously Presented) The method of claim 56, further comprising:

 forming a black matrix layer on the black matrix layer;

 forming a color filter layer on the black matrix layer; and

 forming a liquid crystal layer between the first and second substrates.

68. (Previously Presented) The method of claim 56, further comprising forming a second alignment layer on the second substrate.



69. (Previously Presented) The method of claim 68, wherein the second alignment layer includes one of polyimide, polyamide, polyvinylcinnamate, and polysiloxanecinnamate.